

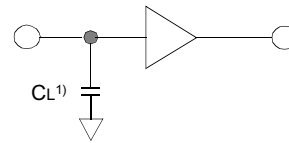
## AC OPERATING CONDITIONS

## TEST CONDITIONS (Test Load and Test Input/Output Reference)

Input pulse level : 0.8 to 2.4V

Input rising and falling time : 5ns

Input and output reference voltage : 1.5V

Output load (See right) :  $C_L=100\text{pF}+1\text{TTL}$   
 $C_L=50\text{pF}+1\text{TTL}$ 

1. Including scope and jig capacitance

AC CHARACTERISTICS ( $V_{CC}=4.5\sim 5.5\text{V}$ , K6T0808C1D-L Family:  $T_A=0$  to  $70^\circ\text{C}$ , K6T0808C1D-P Family:  $T_A=-40$  to  $85^\circ\text{C}$ )

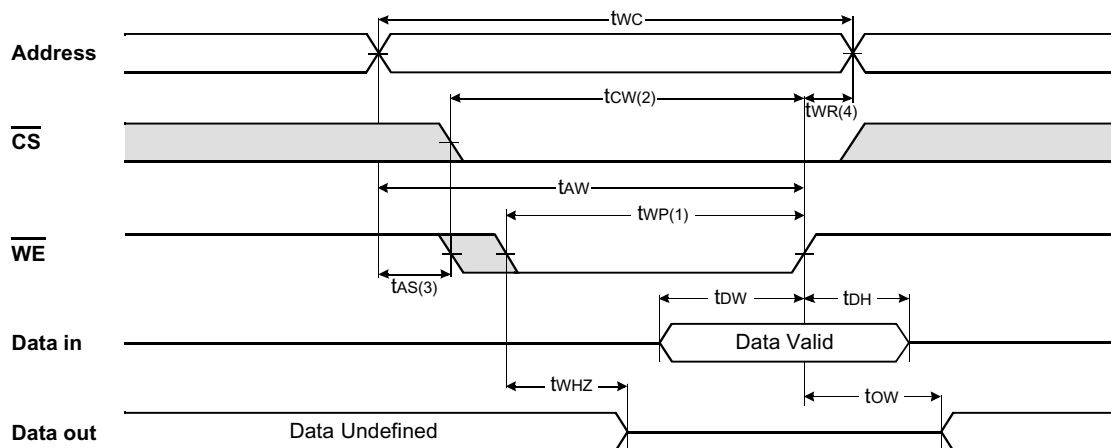
Parameter List		Symbol	Speed Bins				Units
			55 <sup>1)</sup> ns		70ns		
			Min	Max	Min	Max	
Read	Read cycle time	t <sub>RC</sub>	55	-	70	-	ns
	Address access time	t <sub>AA</sub>	-	55	-	70	ns
	Chip select to output	t <sub>CO</sub>	-	55	-	70	ns
	Output enable to valid output	t <sub>OE</sub>	-	25	-	35	ns
	Chip select to low-Z output	t <sub>LZ</sub>	10	-	10	-	ns
	Output enable to low-Z output	t <sub>OLZ</sub>	5	-	5	-	ns
	Chip disable to high-Z output	t <sub>HZ</sub>	0	20	0	30	ns
	Output disable to high-Z output	t <sub>OHZ</sub>	0	20	0	30	ns
	Output hold from address change	t <sub>OH</sub>	10	-	10	-	ns
Write	Write cycle time	t <sub>WC</sub>	55	-	70	-	ns
	Chip select to end of write	t <sub>CW</sub>	45	-	60	-	ns
	Address set-up time	t <sub>AS</sub>	0	-	0	-	ns
	Address valid to end of write	t <sub>AW</sub>	45	-	60	-	ns
	Write pulse width	t <sub>WP</sub>	40	-	50	-	ns
	Write recovery time	t <sub>WR</sub>	0	-	0	-	ns
	Write to output high-Z	t <sub>WHZ</sub>	0	20	0	25	ns
	Data to write time overlap	t <sub>DW</sub>	25	-	30	-	ns
	Data hold from write time	t <sub>DH</sub>	0	-	0	-	ns
	End write to output low-Z	t <sub>OW</sub>	5	-	5	-	ns

1. The parameter is tested with 50pF test load.

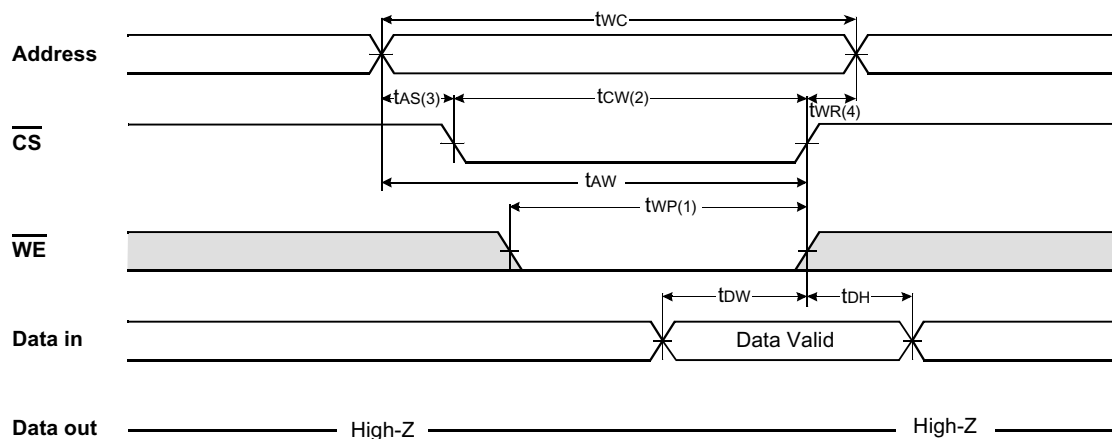
## DATA RETENTION CHARACTERISTICS

Item	Symbol	Test Condition		Min	Typ	Max	Unit
V <sub>CC</sub> for data retention	V <sub>DR</sub>	$\overline{CS} \geq V_{CC}-0.2\text{V}$		2.0	-	5.5	V
Data retention current	I <sub>DR</sub>	$V_{CC}=3.0\text{V}, \overline{CS} \geq V_{CC}-0.2\text{V}$	L-Ver	-	1	15	$\mu\text{A}$
			LL-Ver	-	0.2	3	
Data retention set-up time	t <sub>SDR</sub>	See data retention waveform		0	-	-	ms
Recovery time	t <sub>RDR</sub>			5	-	-	

## TIMING WAVEFORM OF WRITE CYCLE(1) (WE Controlled)



## TIMING WAVEFORM OF WRITE CYCLE(2) ( $\overline{CS}$ Controlled)



### NOTES (WRITE CYCLE)

1. A write occurs during the overlap of a low  $\overline{CS}$  and a low  $\overline{WE}$ . A write begins at the latest transition among  $\overline{CS}$  going Low and  $\overline{WE}$  going low : A write ends at the earliest transition among  $\overline{CS}$  going high and  $\overline{WE}$  going high,  $t_{WP}$  is measured from the beginning of write to the end of write.
2.  $t_{OW}$  is measured from the  $\overline{CS}$  going low to end of write.
3.  $t_{AS}$  is measured from the address valid to the beginning of write.
4.  $t_{WR}$  is measured from the end of write to the address change.  $t_{WR}$  applied in case a write ends as  $\overline{CS}$  or  $\overline{WE}$  going high.

## DATA RETENTION WAVE FORM

### $\overline{CS}$ controlled

